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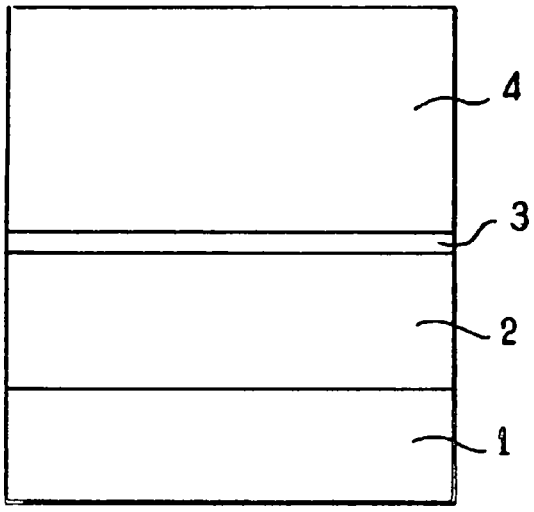
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(54) Title: METHOD OF TRANSFERRING OF A LAYER OF STRAINED SEMICONDUCTOR MATERIAL



(57) Abstract: Method of producing an electronic structure comprising a thin layer of strained semiconductor material from a donor wafer , the donor wafer comprising a lattice parameter matching layer (2) comprising an upper layer of semiconductor material having a first lattice parameter and a film (3) of semiconductor material having a second, nominal, lattice parameter substantially different from the first lattice parameter and strained by the matching layer (2), the process comprising transfer of the film (3) to a receiving substrate (4). Structures produced using one of the processes according to the invention.

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